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(54) Title: GROWTH OF THIN OXIDE LAYER WITH AMORPHOUS SILICON AND OXIDATION

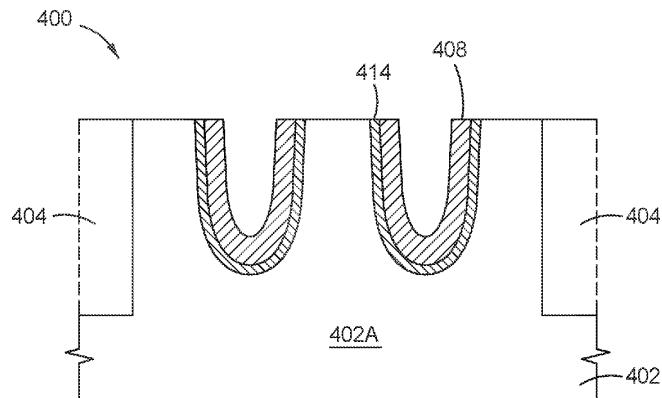


FIG. 4E

(57) Abstract: A method for forming an oxide layer includes forming an interfacial layer on a substrate, forming an amorphous silicon layer on the interfacial layer, performing a direct oxidation process to selectively oxidize the formed amorphous silicon layer, and performing a thermal oxidation process to oxidize the formed amorphous silicon layer.



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